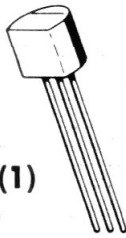


**2N3905 (SILICON)****2N3906****CASE 29(1)**  
(TO-92)

PNP silicon annular transistors, designed for general purpose switching and amplifier applications, features one-piece, injection-molded plastic package for high reliability. The 2N3905 and 2N3906 are complementary with NPN types 2N3903 and 2N3904, respectively.

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Base Voltage	$V_{CB}$	40	Vdc
Emitter-Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current	$I_C$	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ $T_A = 60^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	310	mW
		210	mW
		2.81	mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +135	$^\circ\text{C}$

*www.datasheetcatalog.com***THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$\theta_{JA}$	0.357	$^\circ\text{C}/\text{mW}$

# 2N3905, 2N3906 (continued)

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Fig. No.	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)		BV <sub>CBO</sub>	40	-	Vdc
Collector-Emitter Breakdown Voltage* (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)		BV <sub>CEO</sub> *	40	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)		BV <sub>EBO</sub>	5.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>BE(off)</sub> = 3.0 Vdc)		I <sub>CEX</sub>	-	50	nAdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>BE(off)</sub> = 3.0 Vdc)		I <sub>BL</sub>	-	50	nAdc

### ON CHARACTERISTICS

DC Current Gain* (I <sub>C</sub> = 0.1 mAdc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 1.0 Vdc)  (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc)	2N3905	15	h <sub>FE</sub> *	30	-	-
	2N3906			60	-	-
	2N3905			40	-	-
	2N3906			80	-	-
	2N3905			50	150	-
	2N3906			100	300	-
Collector-Emitter Saturation Voltage* (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)	16, 17	V <sub>CE(sat)</sub> *	-	0.25	Vdc	
Base-Emitter Saturation Voltage* (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)	17	V <sub>BE(sat)</sub> *	0.65	0.85	Vdc	
				-	0.95	

### SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	2N3905 2N3906		f <sub>T</sub>	200 250	-	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 100 kHz)		3	C <sub>ob</sub>	-	4.5	pF
Input Capacitance (V <sub>BE</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 100 kHz)		3	C <sub>ib</sub>	-	10	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	13	h <sub>ie</sub>	0.5 2.0	8.0 12	k ohms
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	14	h <sub>re</sub>	0.1 1.0	5.0 10	X 10 <sup>-4</sup>
Small-Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	11	h <sub>fe</sub>	50 100	200 400	-
Output Admittance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3905 2N3906	12	h <sub>oe</sub>	1.0 3.0	40 60	μmhos
Noise Figure (I <sub>C</sub> = 100 μAdc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 k ohm, f = 10 Hz to 15.7 kHz)	2N3905 2N3906	9, 10	NF	-	5.0 4.0	dB

### SWITCHING CHARACTERISTICS

Delay Time (V <sub>CC</sub> = 3.0 Vdc, V <sub>BE(off)</sub> = 0.5 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)		1, 5	t <sub>d</sub>	-	35	ns
Rise Time		1, 5, 6	t <sub>r</sub>	-	35	ns
Storage Time (V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAdc)	2N3905 2N3906	2, 7	t <sub>s</sub>	-	200 225	ns
Fall Time	2N3905 2N3906	2, 8	t <sub>f</sub>	-	60 75	ns

\* Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

FIGURE 1 — DELAY AND RISE TIME EQUIVALENT TEST CIRCUIT

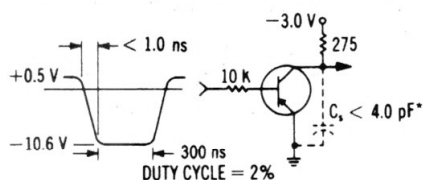
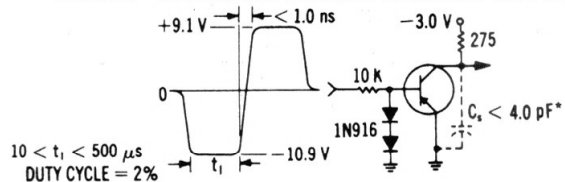


FIGURE 2 — STORAGE AND FALL TIME EQUIVALENT TEST CIRCUIT



\*Total shunt capacitance of test jig and connectors

2N3905, 2N3906 (continued)

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TRANSIENT CHARACTERISTICS  
 —  $T_J = 25^\circ\text{C}$  ---  $T_J = 125^\circ\text{C}$

FIGURE 3 — CAPACITANCE

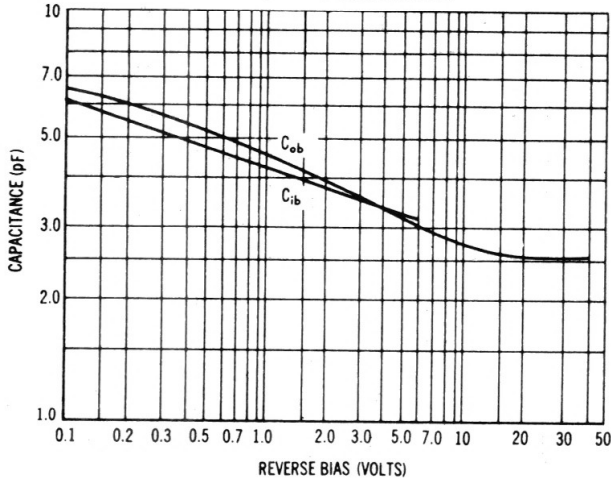


FIGURE 4 — CHARGE DATA

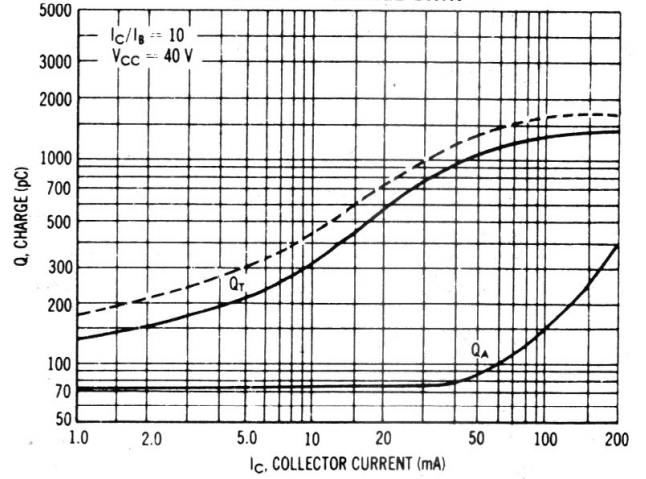


FIGURE 5 — TURN-ON TIME

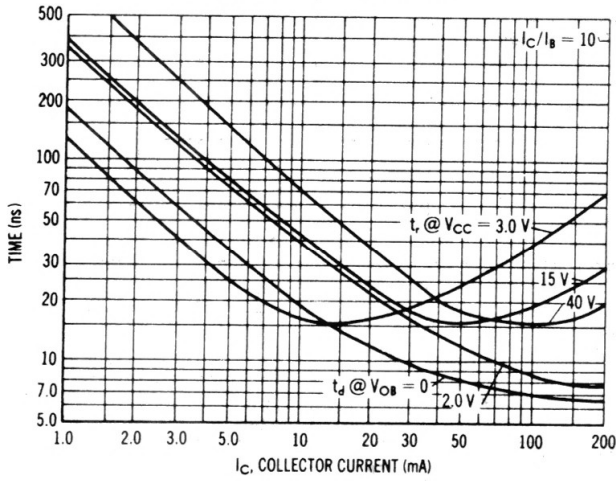


FIGURE 6 — RISE TIME

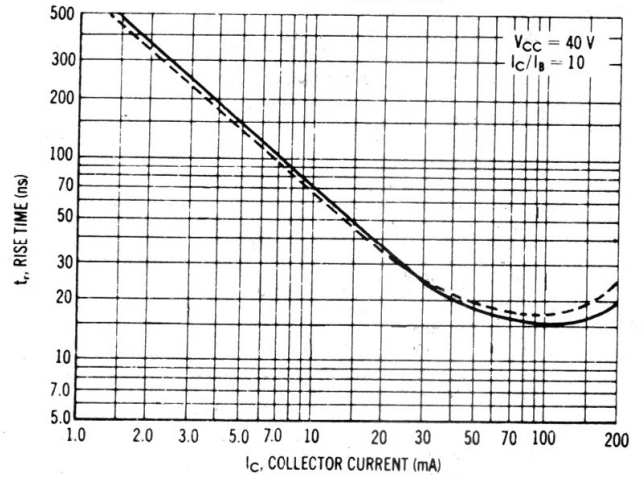


FIGURE 7 — STORAGE TIME

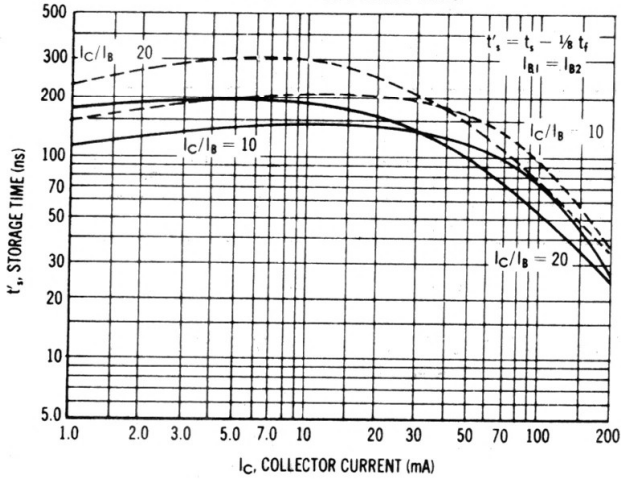
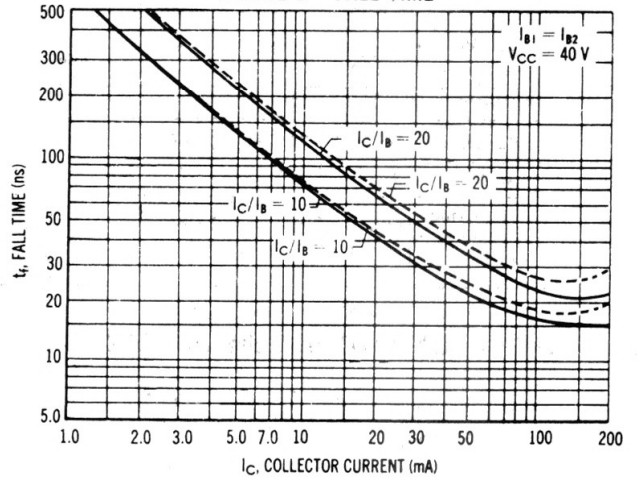


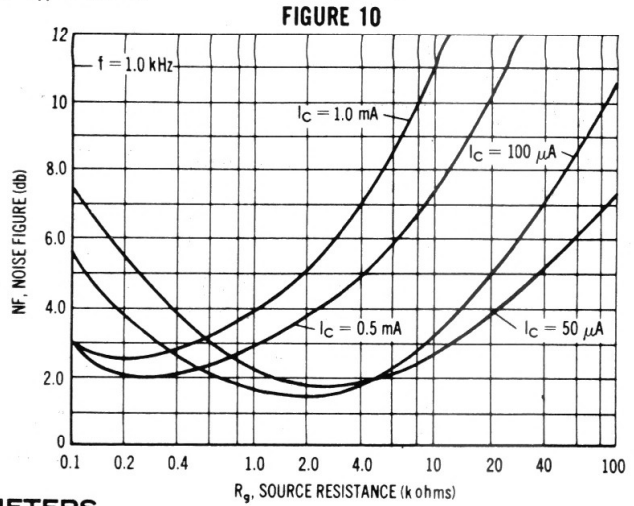
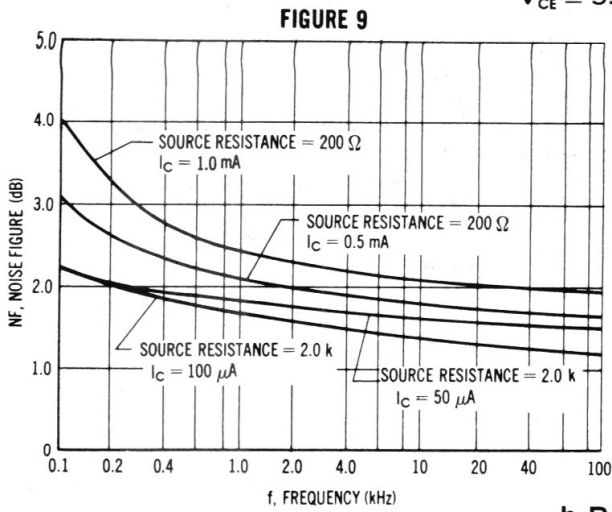
FIGURE 8 — FALL TIME



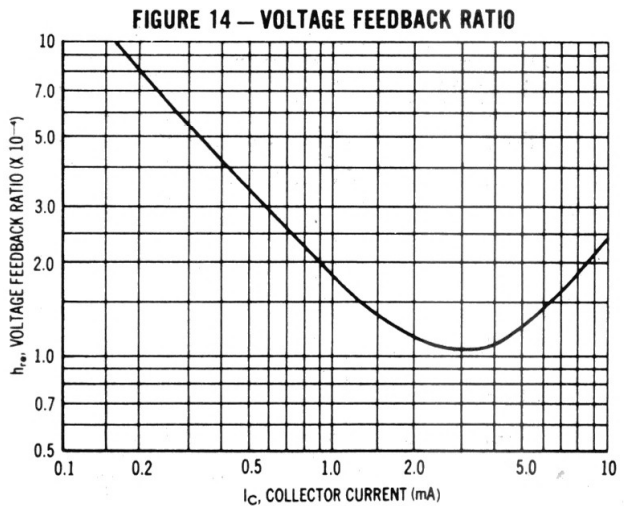
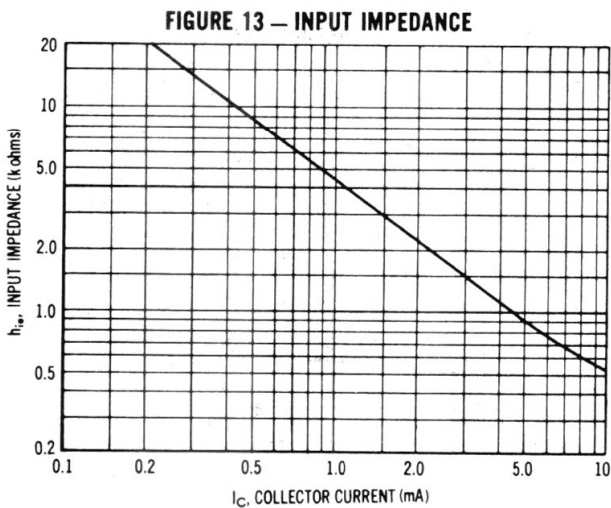
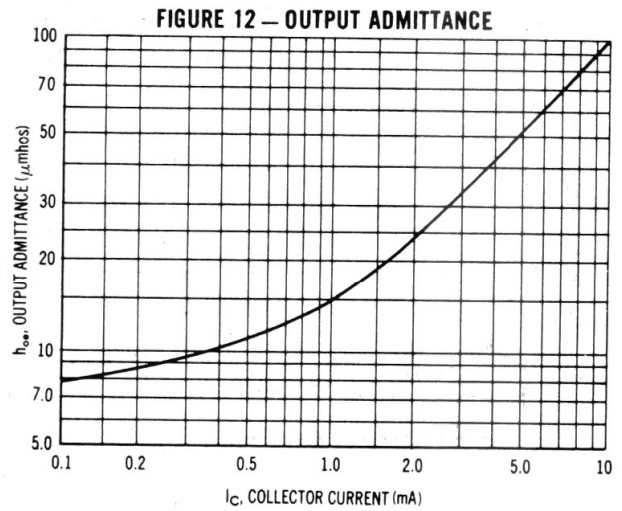
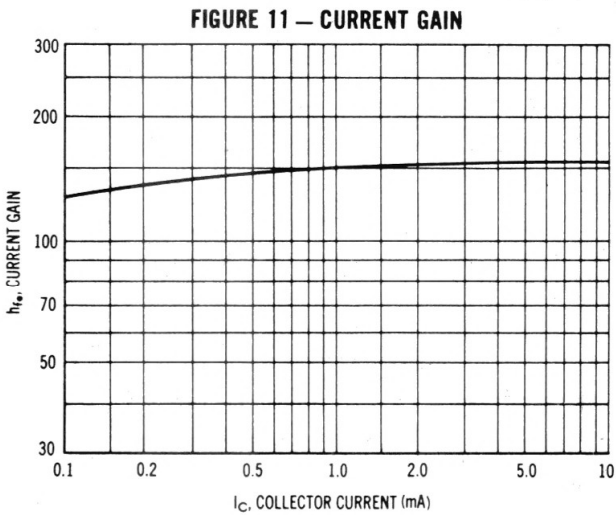


**AUDIO SMALL SIGNAL CHARACTERISTICS**

**NOISE FIGURE VARIATIONS**  
 $V_{CE} = 5.0 \text{ Vdc}, T_A = 25^\circ\text{C}$



**h PARAMETERS**  
 $(V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^\circ\text{C})$



STATIC CHARACTERISTICS

FIGURE 15 — NORMALIZED CURRENT GAIN

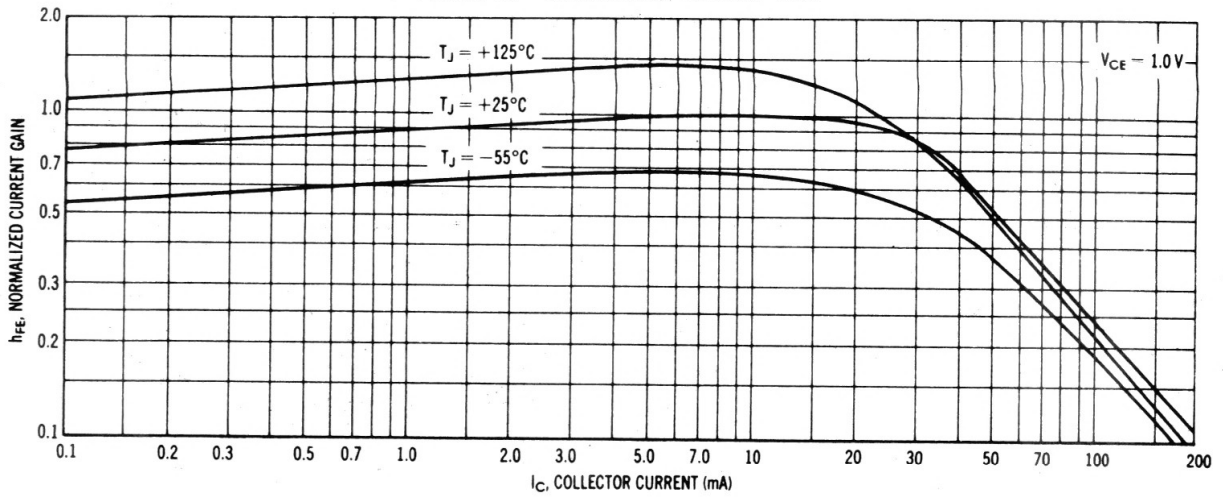


FIGURE 16 — COLLECTOR SATURATION REGION

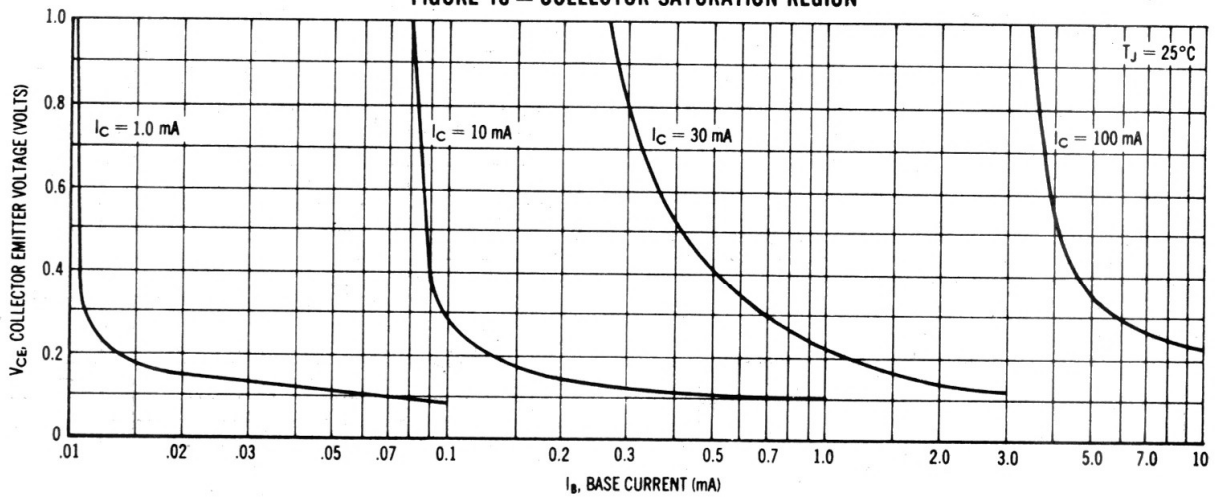


FIGURE 17 — "ON" VOLTAGES

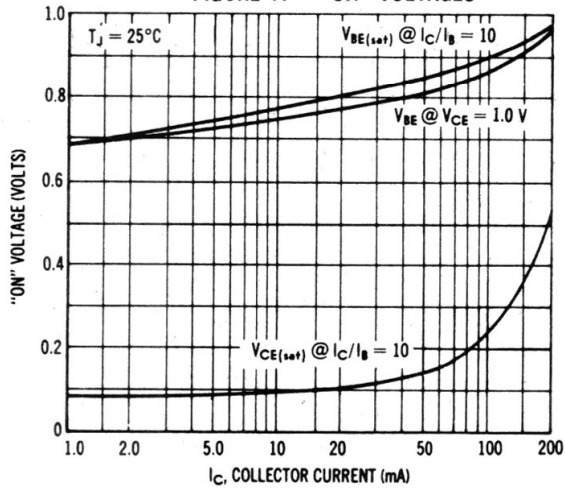


FIGURE 18 — TEMPERATURE COEFFICIENTS

